



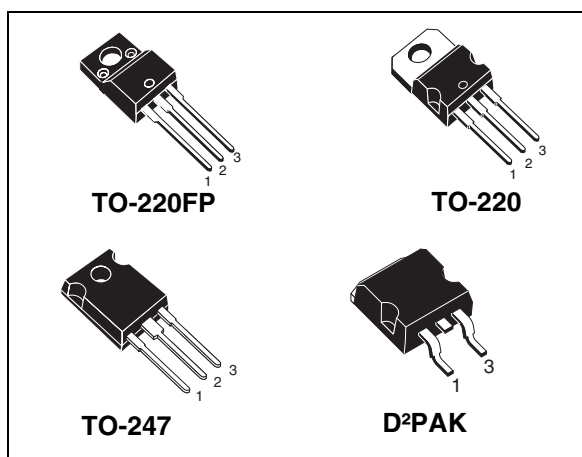
STB23NM50N, STF23NM50N STP23NM50N, STW23NM50N

N-channel 500 V, 0.162 Ω , 17 A TO-220, TO-220FP, TO-247, D²PAK
MDmesh™ II Power MOSFET

Features

Order codes	V _{DSS} (@T _{jmax})	R _{DS(on)} max.	I _D
STB23NM50N	550 V	< 0.19 Ω	17 A
STF23NM50N			
STP23NM50N			
STW23NM50N			

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance



Application

Switching applications

Description

These devices are made using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a new vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

Figure 1. Internal schematic diagram

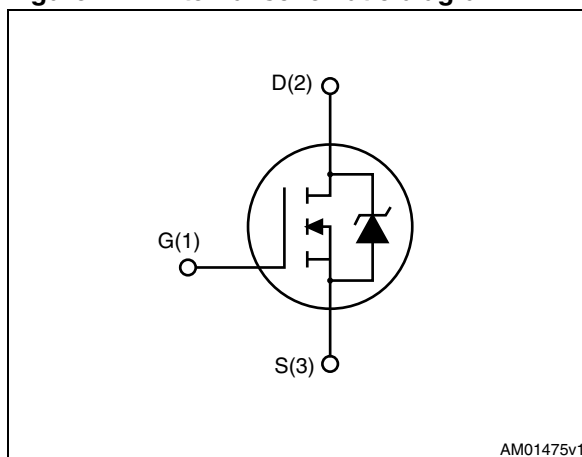


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB23NM50N	23NM50N	D ² PAK	Tape and reel
STF23NM50N		TO-220FP	Tube
STP23NM50N		TO-220	
STW23NM50N		TO-247	

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
2.1	Electrical characteristics (curves)	6
3	Test circuits	9
4	Package mechanical data	10
5	Package mechanical data	15
6	Revision history	16

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value			Unit
		TO-220, D ² PAK	TO-247	TO-220FP	
V _{DS}	Drain-source voltage (V _{GS} = 0)	500			V
V _{GS}	Gate- source voltage	± 25			V
I _D	Drain current (continuous) at T _C = 25 °C	17		17 ⁽¹⁾	A
I _D	Drain current (continuous) at T _C = 100 °C	11		11 ⁽¹⁾	A
I _{DM} ⁽²⁾	Drain current (pulsed)	68		68 ⁽¹⁾	A
P _{TOT}	Total dissipation at T _C = 25 °C	125		30	W
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; T _C =25 °C)			2500	V
dv/dt ⁽³⁾	Peak diode recovery voltage slope	15			V/ns
T _{stg}	Storage temperature	-55 to 150			°C
T _j	Max. operating junction temperature	150			°C

- Limited only by maximum temperature allowed
- Pulse width limited by safe operating area
- I_{SD} ≤ 17 A, di/dt ≤ 400 A/μs, V_{DS peak} ≤ V_{(BR)DSS}, V_{DD} = 80% V_{(BR)DSS}

Table 3. Thermal data

Symbol	Parameter	Value				Unit
		D ² PAK	TO-247	TO-220	TO-220FP	
R _{thj-case}	Thermal resistance junction-case max	1			4.17	°C/W
R _{thj-pcb} ⁽¹⁾	Thermal resistance junction-pcb minimum footprint	30				°C/W
R _{thj-amb}	Thermal resistance junction-ambient max		62.5	50	62.5	°C/W
T _l	Maximum lead temperature for soldering purpose		300			°C

- When mounted on 1inch² FR-4 board, 2 oz Cu

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I _{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T _j Max)	6	A
E _{AS}	Single pulse avalanche energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	254	mJ

2 Electrical characteristics

($T_{CASE}=25\text{ °C}$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	500			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{max rating}$ $V_{DS} = \text{max rating}$, @125 °C			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 25\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 8.5\text{ A}$		0.162	0.19	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 50\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	1330	-	pF
C_{oss}	Output capacitance			84		pF
C_{rss}	Reverse transfer capacitance			4.8		pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0$, $V_{DS} = 0\text{ to }400\text{ V}$	-	210	-	pF
Q_g	Total gate charge	$V_{DD} = 400\text{ V}$, $I_D = 17\text{ A}$, $V_{GS} = 10\text{ V}$, <i>(see Figure 18)</i>	-	45	-	nC
Q_{gs}	Gate-source charge			7		nC
Q_{gd}	Gate-drain charge			24		nC
R_g	Gate input resistance	f=1 MHz Gate DC Bias=0 Test signal level=20 mV open drain	-	4.6	-	Ω

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 250\text{ V}$, $I_D = 17\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 17)	-	6.6	-	ns
t_r	Rise time			19		ns
$t_{d(off)}$	Turn-off-delay time			71		ns
t_f	Fall time			29		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current		-		17	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				68	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 17\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 17\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see Figure 22)	-	286		ns
Q_{rr}	Reverse recovery charge			3700		nC
I_{RRM}	Reverse recovery current			26		A
t_{rr}	Reverse recovery time	$I_{SD} = 17\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 22)	-	350		ns
Q_{rr}	Reverse recovery charge			4800		nC
I_{RRM}	Reverse recovery current			27		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, D²PAK

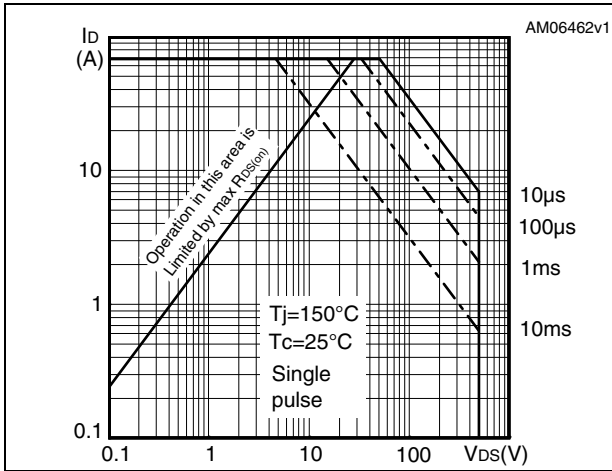


Figure 3. Thermal impedance for TO-220, D²PAK

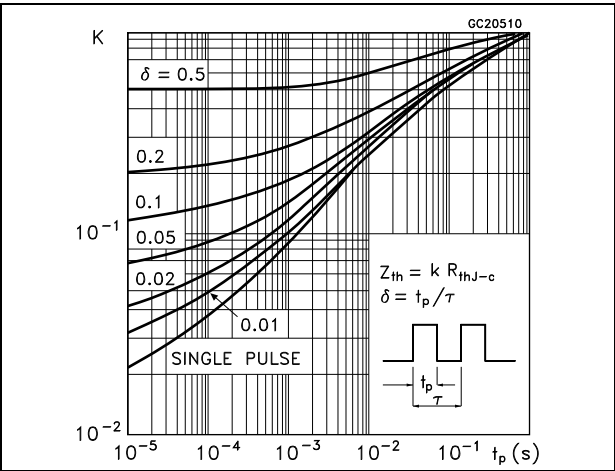


Figure 4. Safe operating area for TO-220FP

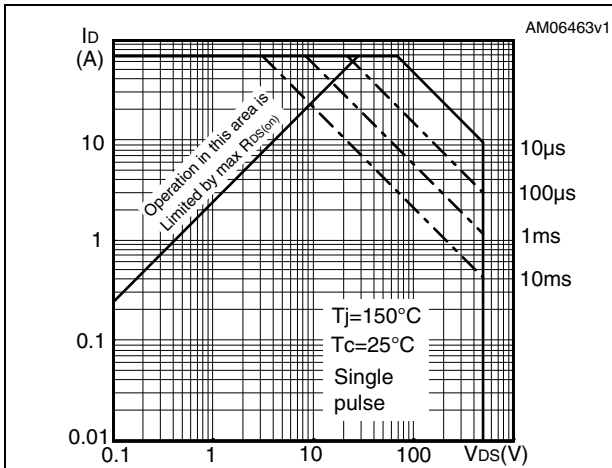


Figure 5. Thermal impedance for TO-220FP

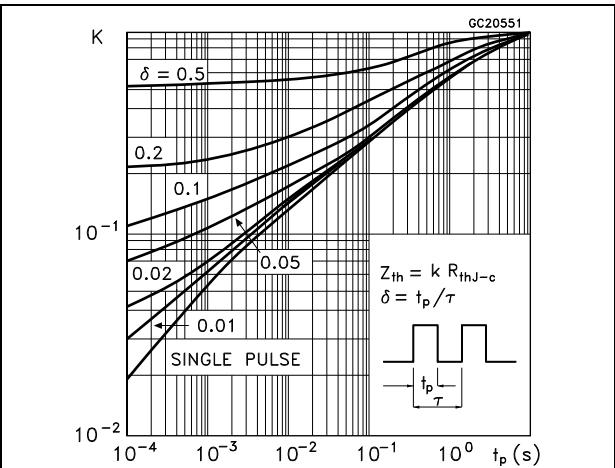


Figure 6. Safe operating area for TO-247

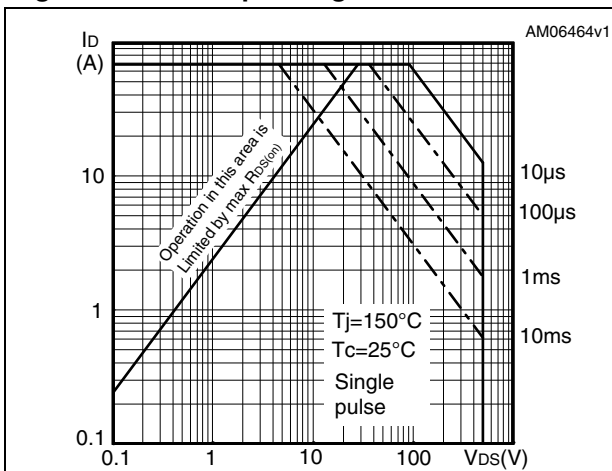


Figure 7. Thermal impedance for TO-247

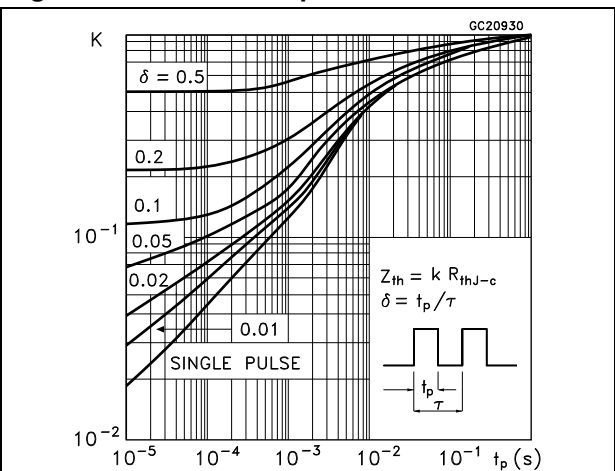


Figure 8. Output characteristics

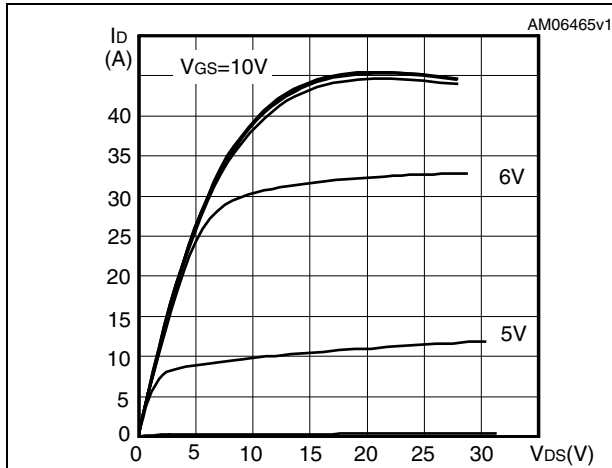


Figure 9. Transfer characteristics

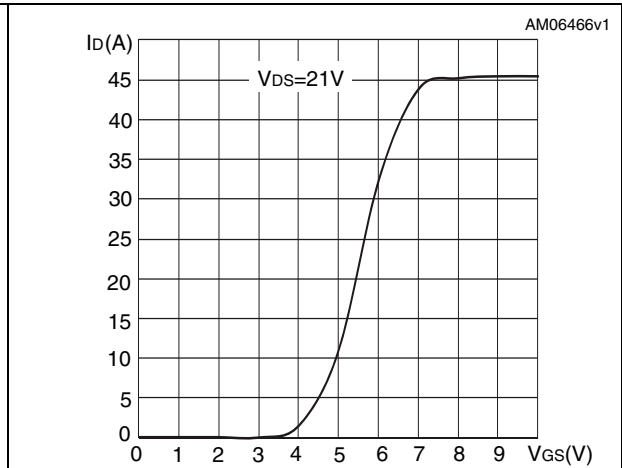


Figure 10. Normalized $B_{V_{DSS}}$ vs temperature

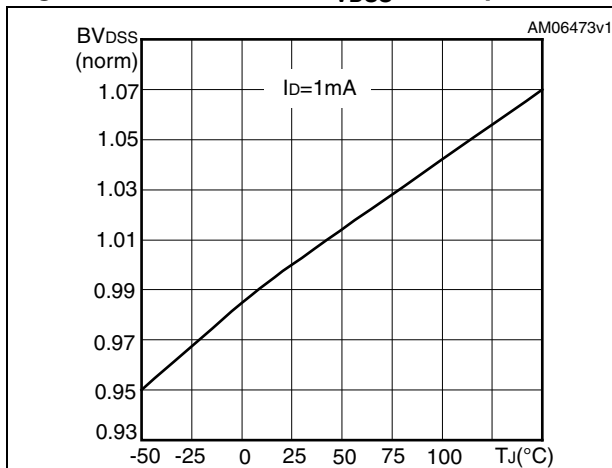


Figure 11. Static drain-source on resistance

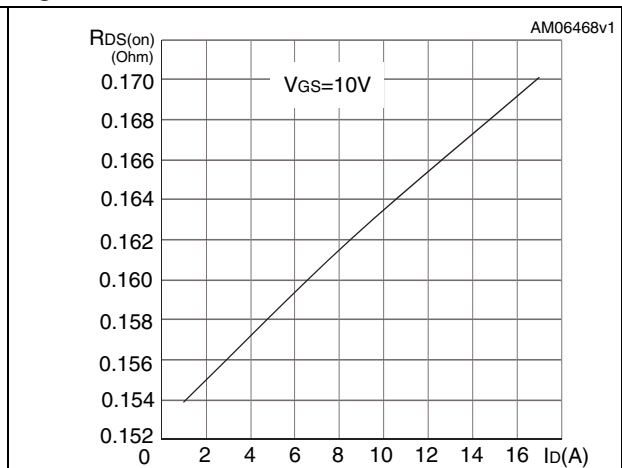


Figure 12. Gate charge vs gate-source voltage

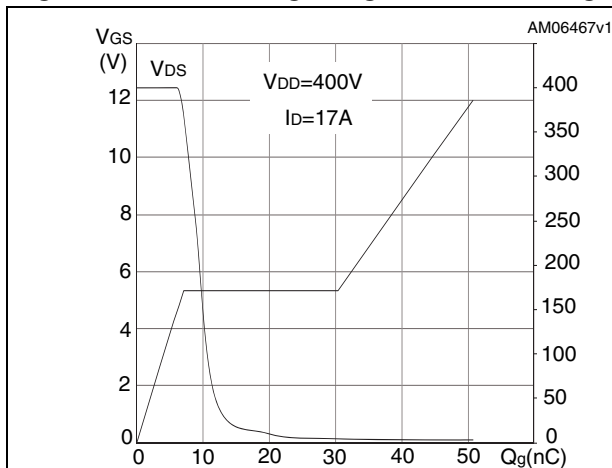


Figure 13. Capacitance variations

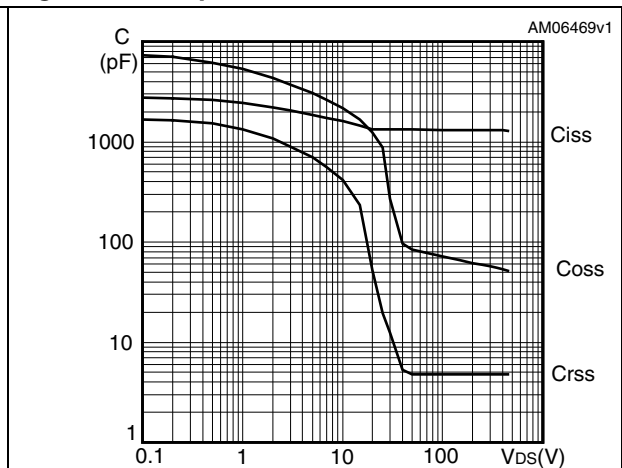


Figure 14. Normalized gate threshold voltage vs temperature

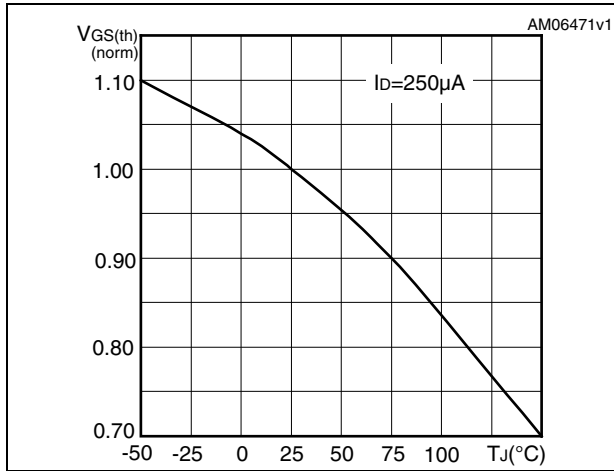


Figure 15. Normalized on resistance vs temperature

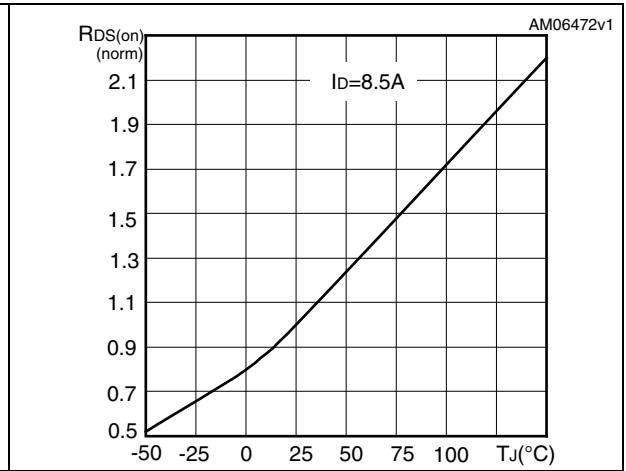
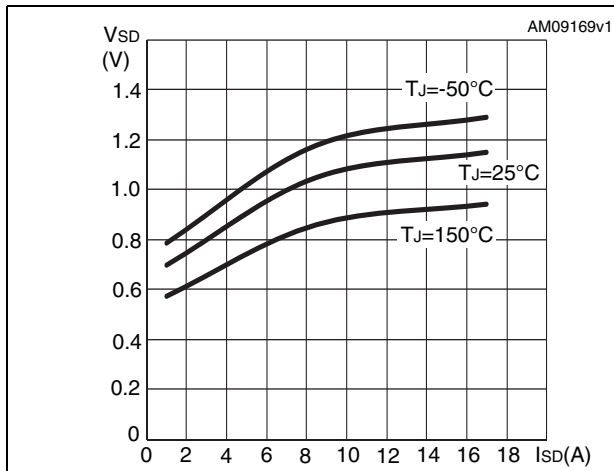
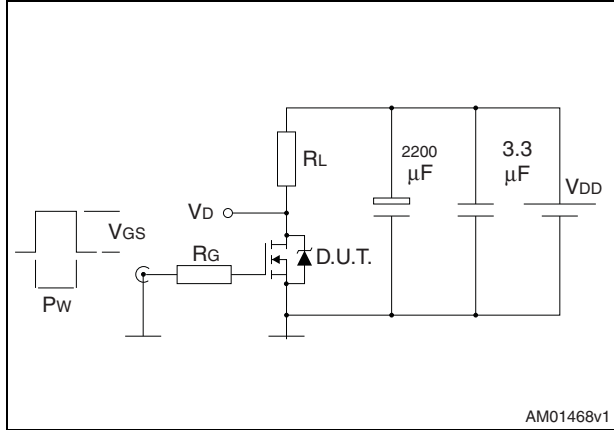


Figure 16. Source-drain diode forward characteristics



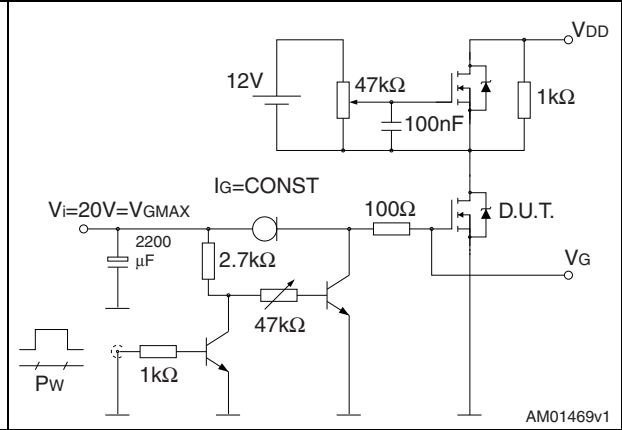
3 Test circuits

Figure 17. Switching times test circuit for resistive load



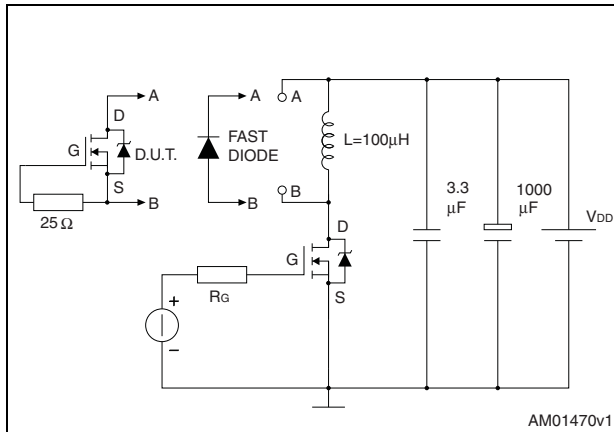
AM01468v1

Figure 18. Gate charge test circuit



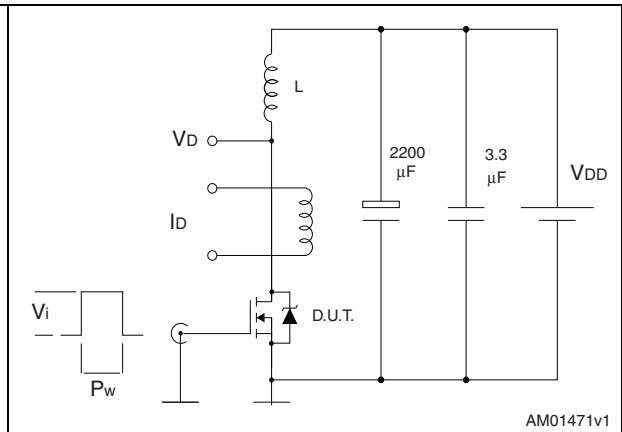
AM01469v1

Figure 19. Test circuit for inductive load switching and diode recovery times



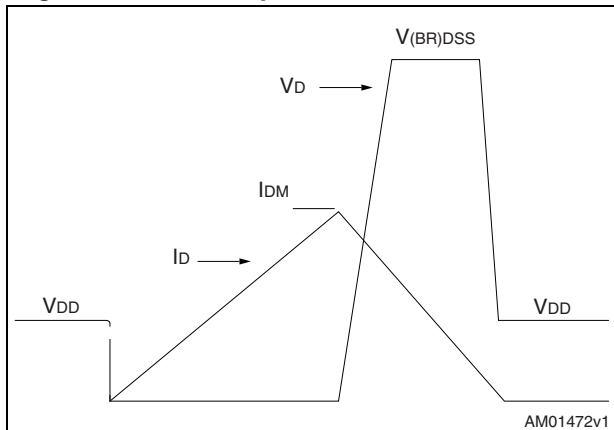
AM01470v1

Figure 20. Unclamped inductive load test circuit



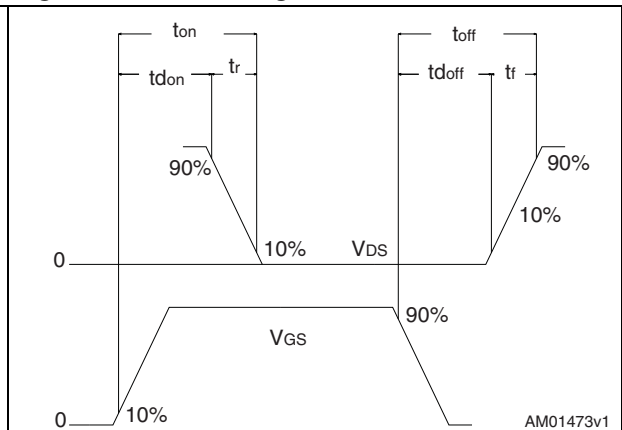
AM01471v1

Figure 21. Unclamped inductive waveform



AM01472v1

Figure 22. Switching time waveform



AM01473v1

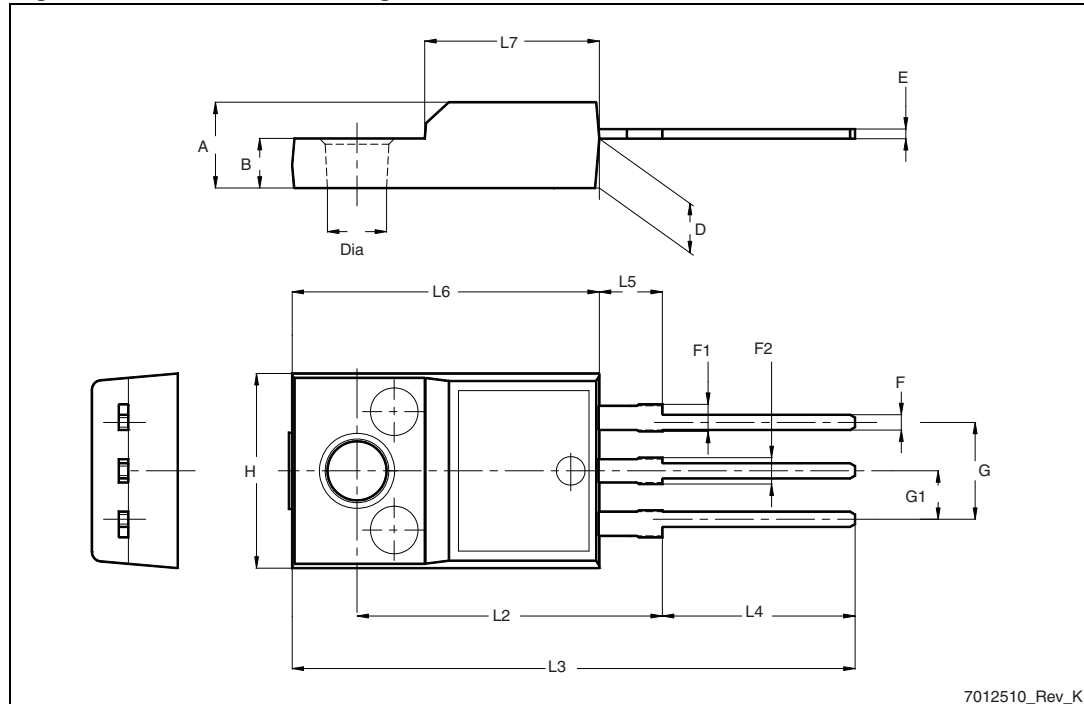
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 9. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 23. TO-220FP drawing



7012510_Rev_K

Table 10. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 24. TO-220 type A drawing

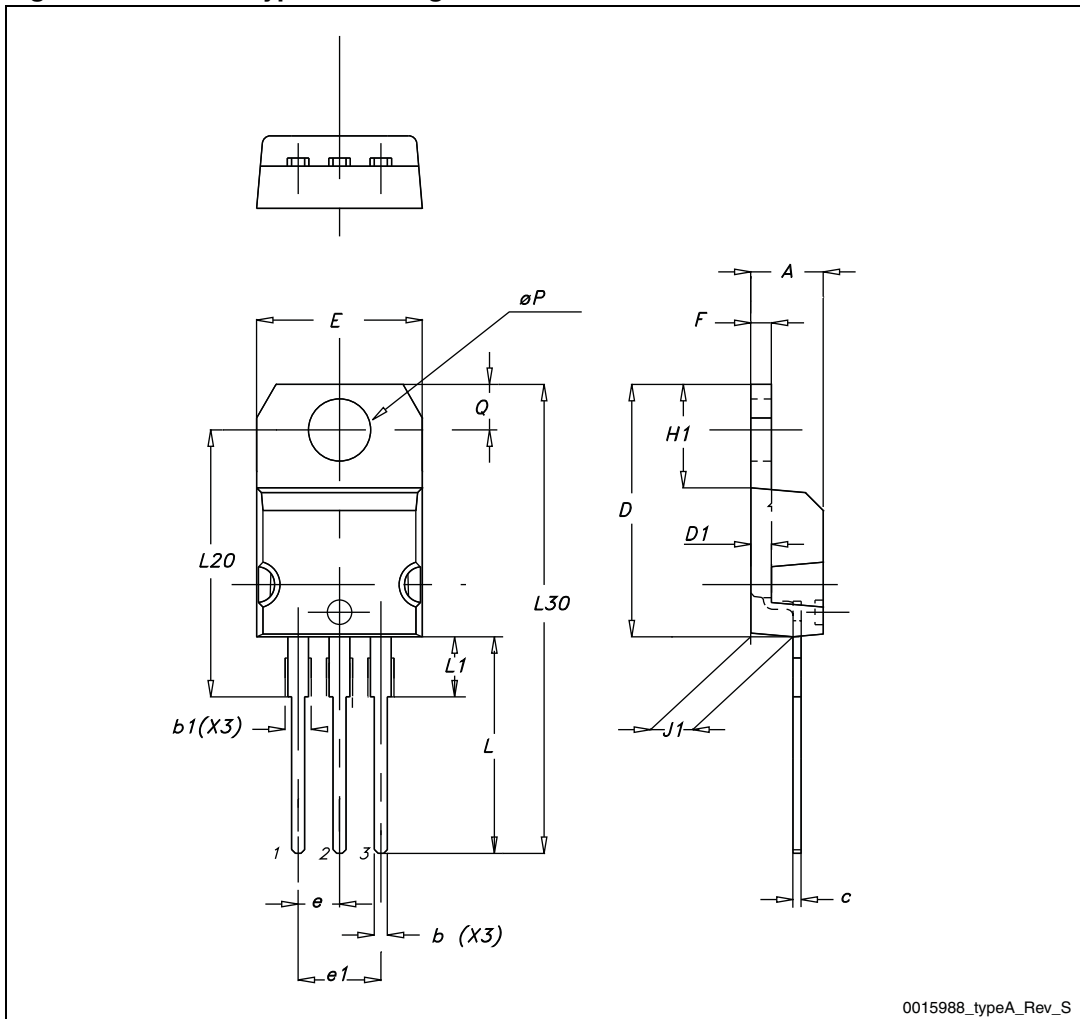


Table 11. TO-247 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S		5.50	

Figure 25. TO-247 drawing

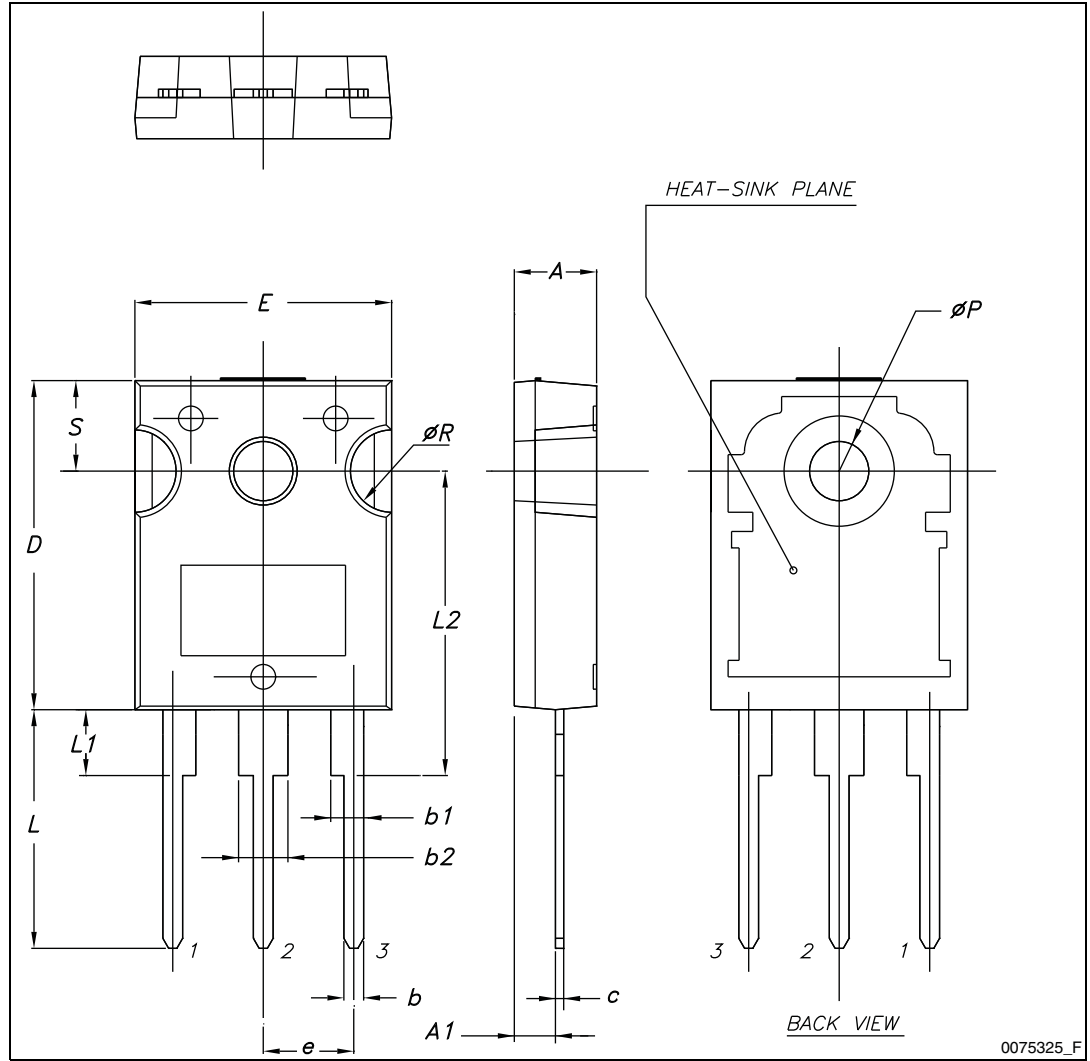


Table 12. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 26. D²PAK footprint^(a)

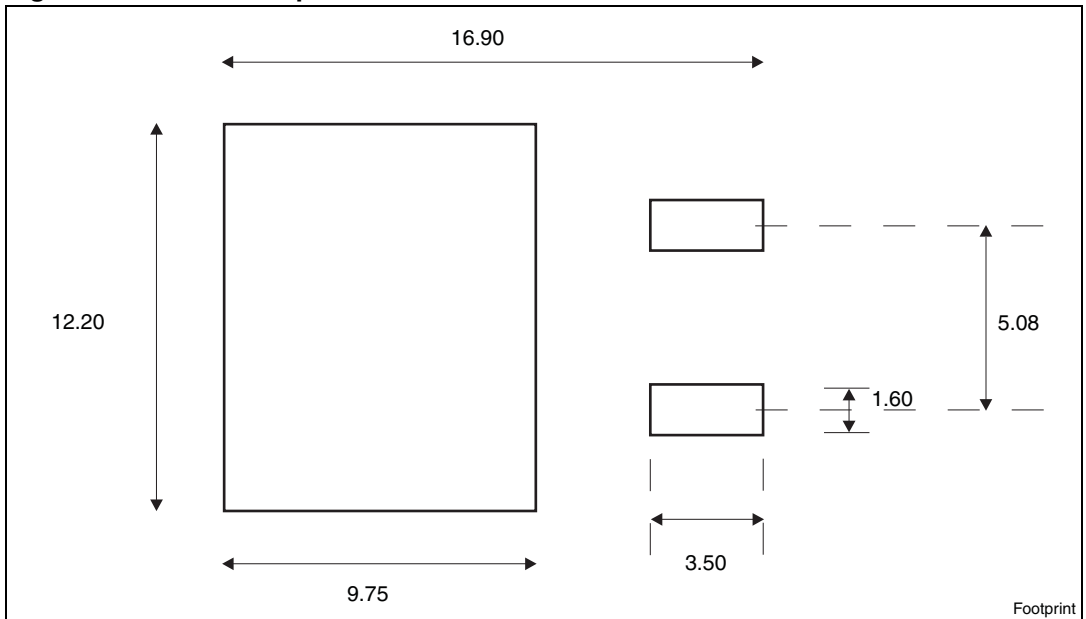
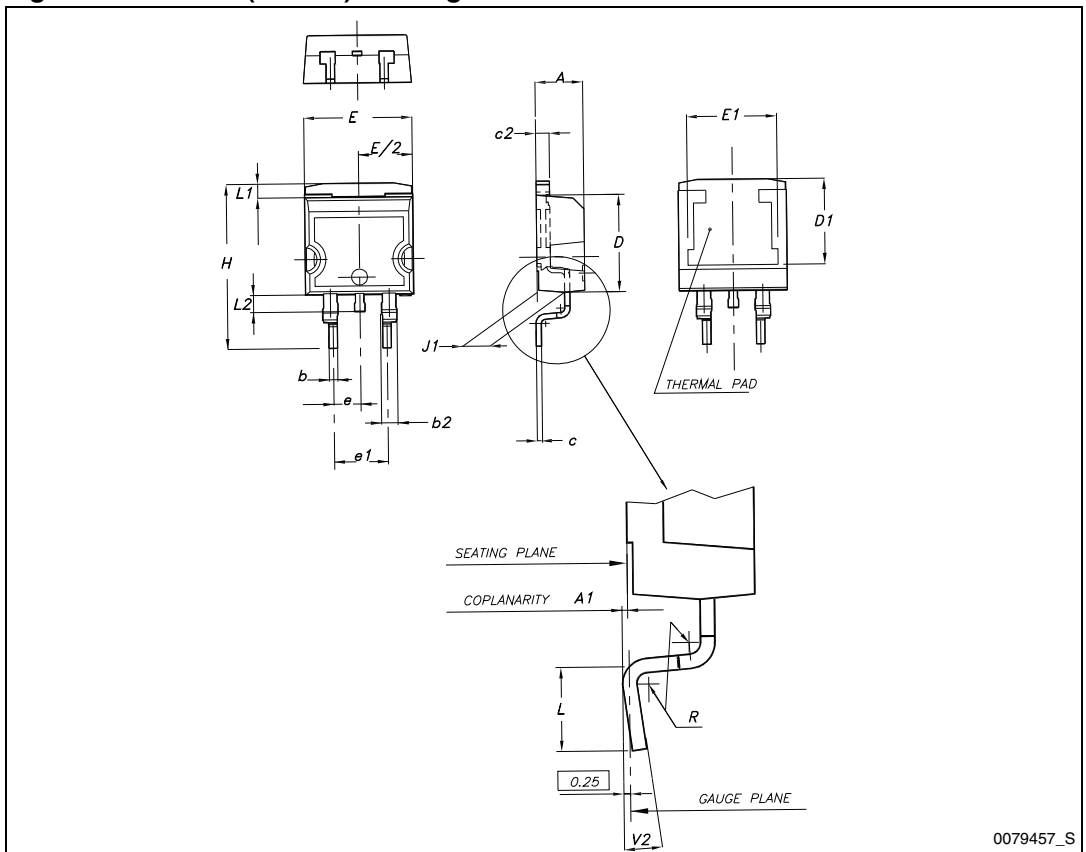


Figure 27. D²PAK (TO-263) drawing



a. All dimension are in millimeters

5 Package mechanical data

Table 13. D²PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1		Base qty	1000
P2	1.9	2.1		Bulk qty	1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 28. Tape

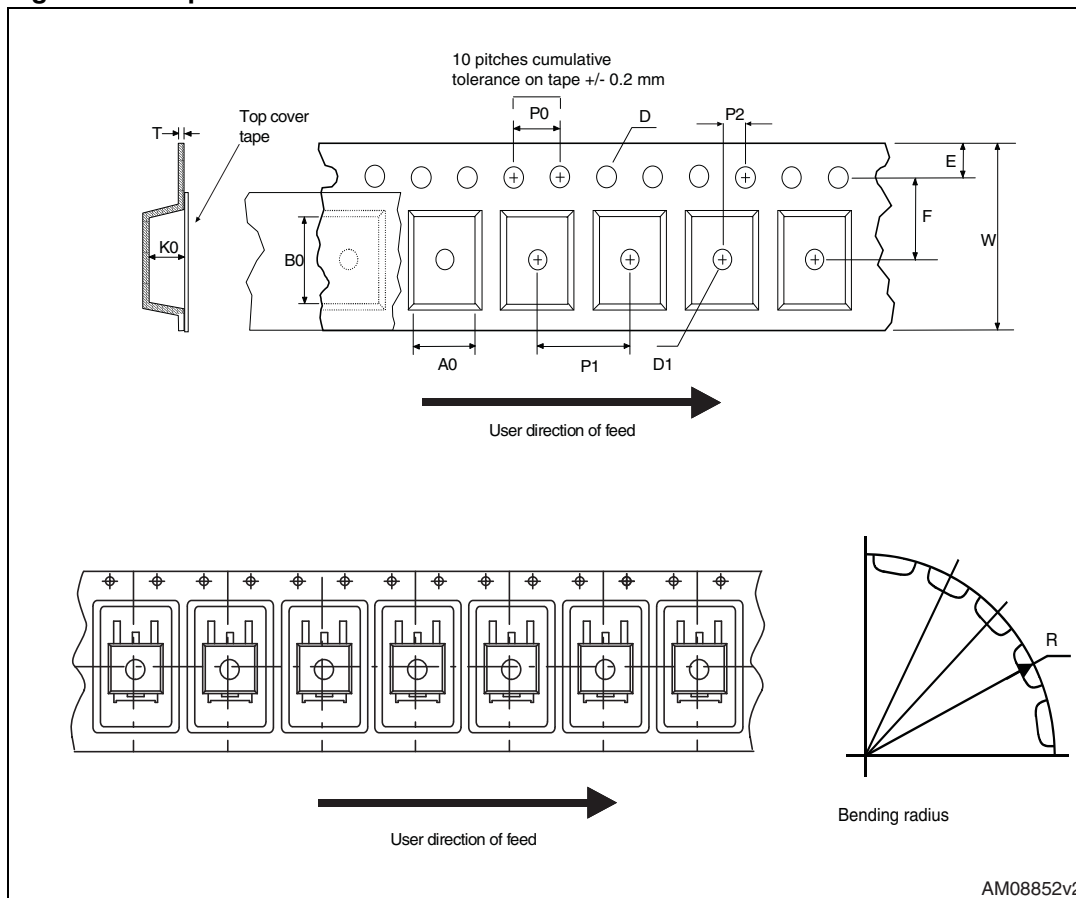
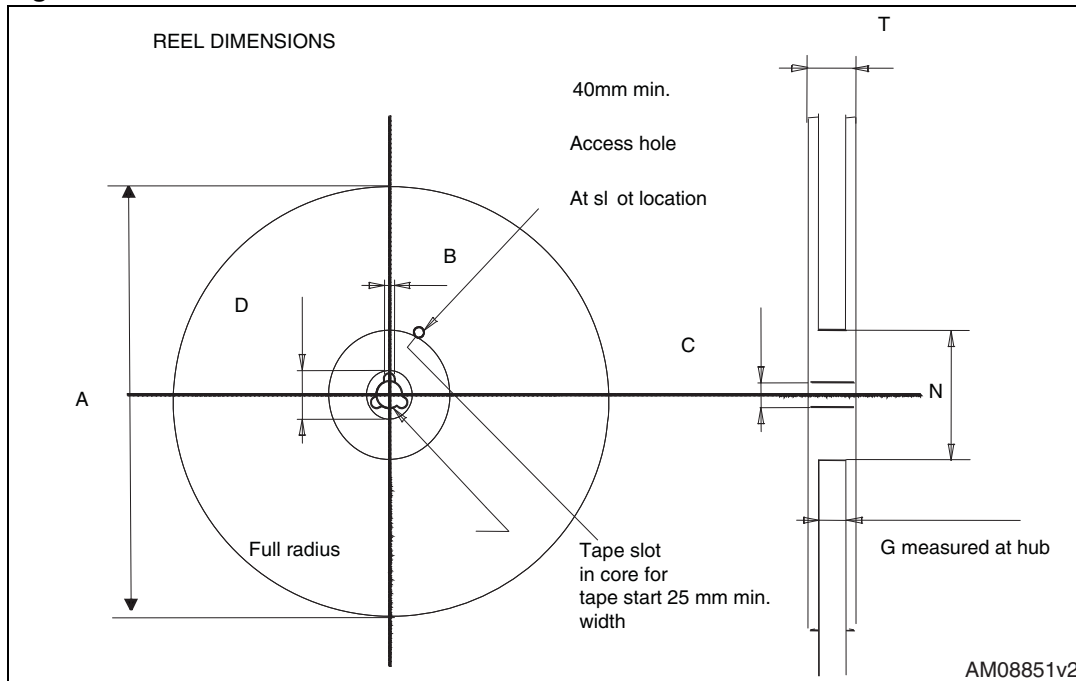


Figure 29. Reel



6 Revision history

Table 14. Document revision history

Date	Revision	Changes
11-Dec-2009	1	First release.
26-May-2010	2	Document status promoted from preliminary data to datasheet.
16-Sep-2010	3	Added new value in <i>Figure 14</i> , <i>Figure 15</i> and <i>Figure 10</i> .
23-May-2011	4	<i>Section 2.1: Electrical characteristics (curves)</i> has been updated.

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2011 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.